

To all our customers

Regarding the change of names mentioned in the document, such as Mitsubishi Electric and Mitsubishi XX, to Renesas Technology Corp.

The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

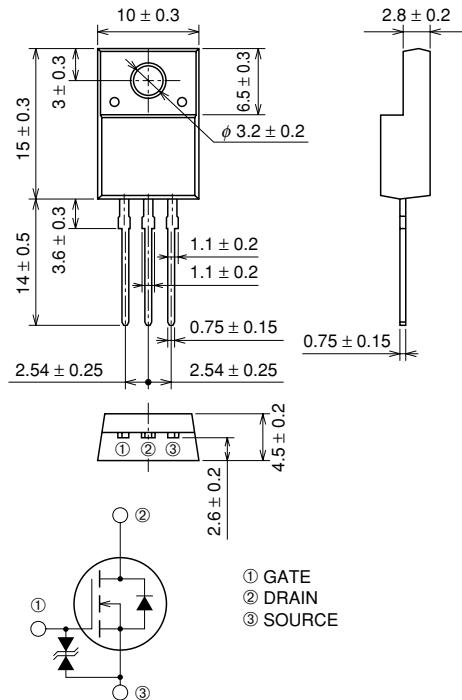
FL14KM-9A



- 10V DRIVE
- V_{DSS} 450V
- $r_{DS\ (ON)\ (MAX)}$ 0.52Ω
- I_D 14A

OUTLINE DRAWING

Dimensions in mm



APPLICATION

SMPS, Inverter fluorescent light sets, etc.

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DSS}	Drain-source voltage	$V_{GS} = 0\text{V}$	450	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0\text{V}$	± 30	V
I_D	Drain current		14	A
I_{DM}	Drain current (Pulsed)		42	A
I_{DA}	Avalanche current (Pulsed)	$L = 200\mu\text{H}$	14	A
P_D	Maximum power dissipation		40	W
T_{ch}	Channel temperature		$-55 \sim +150$	°C
T_{stg}	Storage temperature		$-55 \sim +150$	°C
V_{iso}	Isolation voltage	AC for 1 minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	ID = 1mA, VGS = 0V	450	—	—	V
V (BR) GSS	Gate-source breakdown voltage	IG = ±100µA, VDS = 0V	±30	—	—	V
IGSS	Gate-source leakage current	VGS = ±25V, VDS = 0V	—	—	±10	µA
IDSS	Drain-source leakage current	VDS = 450V, VGS = 0V	—	—	1	mA
VGS (th)	Gate-source threshold voltage	ID = 1mA, VDS = 10V	2.0	3.0	4.0	V
rDS (ON)	Drain-source on-state resistance	ID = 7A, VGS = 10V	—	0.40	0.52	Ω
VDS (ON)	Drain-source on-state voltage	ID = 7A, VGS = 10V	—	2.80	3.64	V
yfs	Forward transfer admittance	ID = 7A, VDS = 10V	—	8.0	—	S
Ciss	Input capacitance	VDS = 25V, VGS = 0V, f = 1MHz	—	1250	—	pF
Coss	Output capacitance		—	150	—	pF
Crss	Reverse transfer capacitance		—	55	—	pF
td (on)	Turn-on delay time	VDD = 200V, ID = 7A, VGS = 10V, RGEN = RGS = 50Ω	—	25	—	ns
tr	Rise time		—	45	—	ns
td (off)	Turn-off delay time		—	250	—	ns
tf	Fall time		—	90	—	ns
VSD	Source-drain voltage	IS = 7A, VGS = 0V	—	1.5	2.0	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	3.13	°C/W